



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

FMMT593

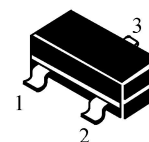
## SOT-23 Bipolar Transistor 双极型三极管

### ■ Features 特点

PNP Low equivalent on-resistance 低等效电阻

## SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



### ■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	-120	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	-100	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	-5	V
Collector Current 集电极电流	$I_C$	-1000	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	250	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ\text{C}$	

### ■ Device Marking 产品打标

FMMT593=593

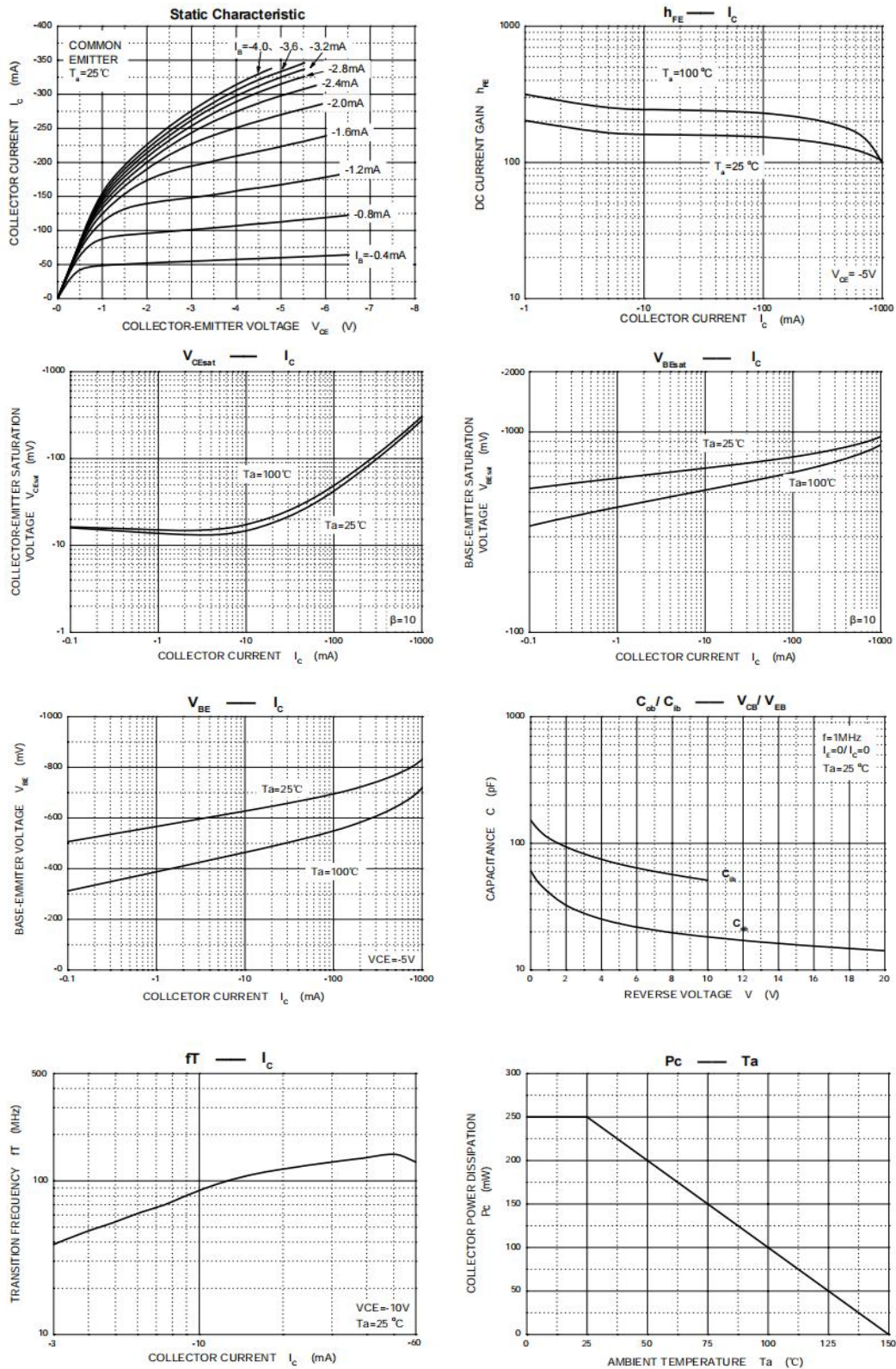


## ■ Electrical Characteristics 电特性

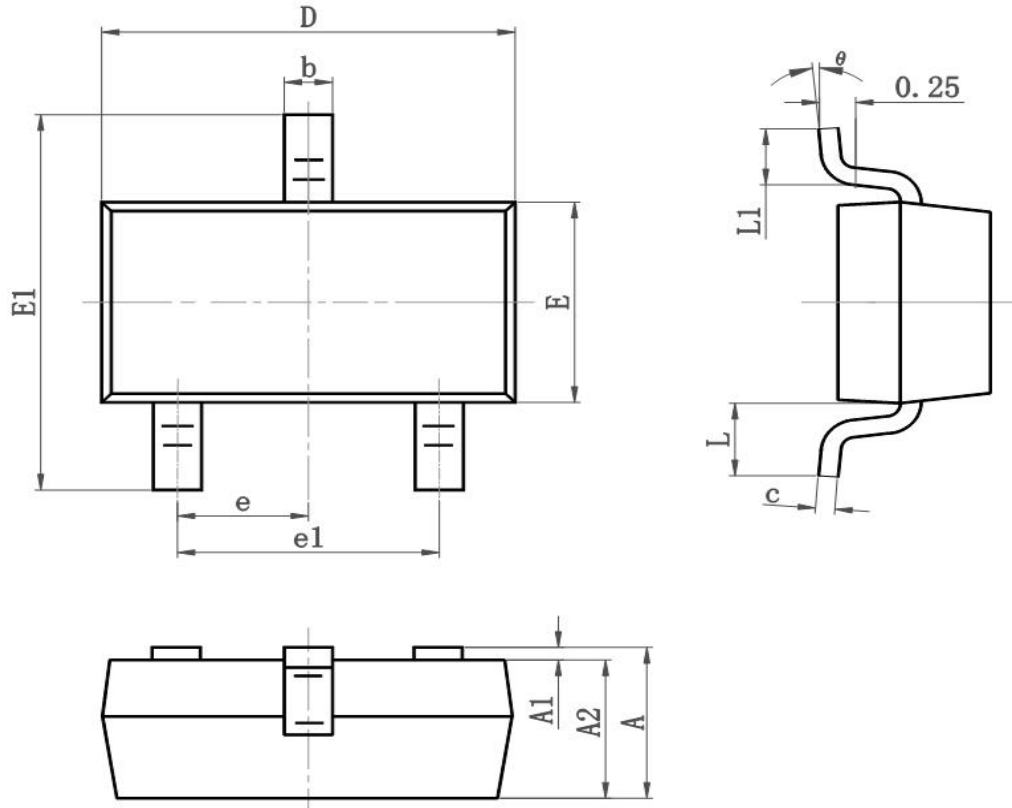
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压( $I_C = -100\mu\text{A}$ , $I_E = 0$ )	$BV_{CBO}$	-120	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压( $I_C = -10\text{mA}$ , $I_B = 0$ )	$BV_{CEO}$	-100	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压( $I_E = -100\mu\text{A}$ , $I_C = 0$ )	$BV_{EBO}$	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流( $V_{CB} = -100\text{V}$ , $I_E = 0$ )	$I_{CBO}$	—	—	-100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流( $V_{CE} = -100\text{V}$ , $V_{BE} = 0\text{V}$ )	$I_{CES}$	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流( $V_{EB} = -4\text{V}$ , $I_C = 0$ )	$I_{EBO}$	—	—	-100	nA
DC Current Gain( $V_{CE} = -5\text{V}$ , $I_C = -1\text{mA}$ ) 直流电流增益( $V_{CE} = -5\text{V}$ , $I_C = -250\text{mA}$ ) ( $V_{CE} = -5\text{V}$ , $I_C = -500\text{mA}$ ) ( $V_{CE} = -5\text{V}$ , $I_C = -1000\text{mA}$ )	$H_{FE}$	100 100 100 50	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ( $I_C = -250\text{mA}$ , $I_B = -25\text{mA}$ ) ( $I_C = -500\text{mA}$ , $I_B = -50\text{mA}$ )	$V_{CE(sat)}$	—	—	-0.2 -0.3	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ( $I_C = -500\text{mA}$ , $I_B = -50\text{mA}$ )	$V_{BE(sat)}$	—	—	-1.1	V
Base-Emitter On Voltage 基极发射极导通电压 ( $V_{CE} = -5\text{V}$ , $I_C = -1000\text{mA}$ )	$V_{BE(on)}$	—	—	-1	V
Transition Frequency 特征频率( $V_{CE} = -10\text{V}$ , $I_C = -50\text{mA}$ )	$f_T$	50	—	—	MHz
Output Capacitance 输出电容( $V_{CB} = -10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$ )	$C_{ob}$	—	5	—	pF

## Typical Characteristic Curve 典型特性曲线



## ■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°